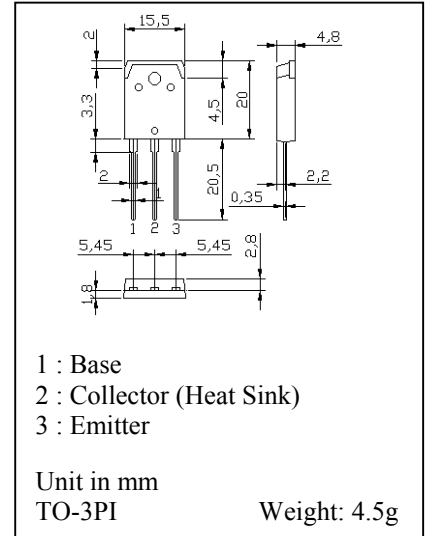


**PNP SILICON TRIPLE DIFFUSED TRANSISTOR**

...designed for power amplifier applications.

**FEATURE:**

- High Collector Voltage:  $V_{CE0} = -180V$  (Min.)
- Complementary to PMC3907
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.



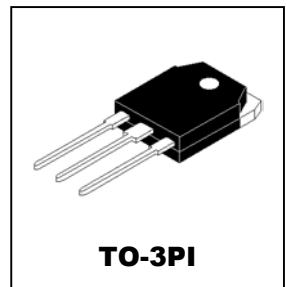
**MAXIMUM RATINGS ( $T_a = 25\text{ }^\circ\text{C}$ )**

| Characteristic   | Symbol    | Value     | Unit             |
|--|-----------|-----------|------------------|
| Collector Base Voltage                                       | $V_{CBO}$ | -180      | V                |
| Collector Emitter Voltage                                    | $V_{CEO}$ | -180      | V                |
| Emitter Base Voltage   | $V_{EBO}$ | -5        | V                |
| Collector Current  | $I_c$     | -12       | A                |
| Base Current   | $I_b$     | -1.2      | A                |
| Collector power Dissipation $T_c = 25\text{ }^\circ\text{C}$ | $P_c$     | 130       | W                |
| Junction Temperature   | $T_j$     | 150       | $^\circ\text{C}$ |
| Storage Temperature Range                                    | $T_{stg}$ | -55 ~ 150 | $^\circ\text{C}$ |

**ELECTRICAL CHARACTERISTICS ( $T_a = 25\text{ }^\circ\text{C}$ )**

| Characteristic                       | Symbol        | Test Condition                            | Min. | Typ. | Max. | Unit          |
|--------------------------------------|---------------|---|------|------|------|---------------|
| Collector Cutoff Current             | $I_{CBO}$     | $V_{CB} = -180V, I_E = 0$                 | -    | -    | -5   | $\mu\text{A}$ |
| Emitter Cutoff Current               | $I_{EBO}$     | $V_{EB} = -5V, I_C = 0$                   | -    | -    | -5   | $\mu\text{A}$ |
| Collector Emitter Breakdown Voltage  | $V_{(BR)CEO}$ | $I_c = -50\text{mA}, I_b = 0$             | -180 | -    | -    | V             |
| DC Current Gain                      | $h_{FE(1)}$   | $V_{CE} = -5V, I_c = -1A$                 | 55   | -    | 180  | -             |
|                                      | $h_{FE(2)}$   | $V_{CE} = -5V, I_c = -7A$                 | 35   | 80   | -    | -             |
| Collector Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_c = -8A, I_b = -0.8A$                  | -    | -1.5 | -3   | V             |
| Base Emitter Voltage                 | $V_{BE}$      | $V_{CE} = -5V, I_c = -7A$                 | -    | -1   | -1.5 | V             |
| Transition Frequency                 | $f_T$         | $V_{CE} = -5V, I_E = -1A$                 | -    | 25   | -    | MHz           |
| Collector Output Capacitance         | $C_{ob}$      | $V_{CB} = -10V, I_E = 0, f = 1\text{MHz}$ | -    | 470  | -    | pF            |

**PNP SILICON TRIPLE DIFFUSED TRANSISTOR**



**Classification of  $h_{FE(1)}$**

| Class       | R         | O         |
|-------------|-----------|-----------|
| $h_{FE(1)}$ | 55 to 110 | 90 to 180 |

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